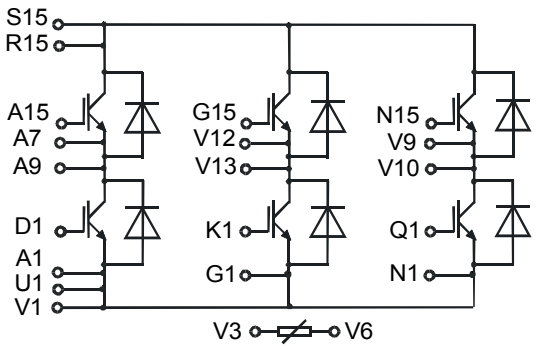
IGBT Module

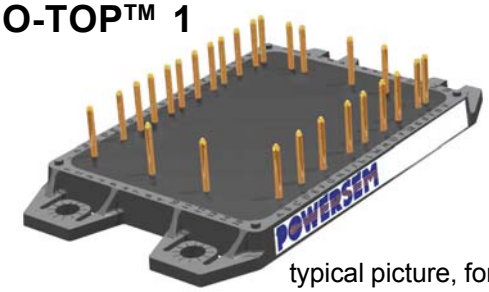
Preliminary Data Sheet

PSII 75/12*

I_{C80} = 60 A
V_{CES} = 1200 V
$V_{CE(sat)typ.}$ = 2.7 V



ECO-TOP™ 1



typical picture, for pin configuration see outline drawing

*NTC optional

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	1200	V
V_{GES}		± 20	V
I_{C25}	T_C = 25°C	90	A
I_{C80}	T_C = 80°C	60	A
I_{CM}	V_{GE} = ±15 V; R_G = 22 Ω; T_{VJ} = 125°C	100	A
V_{CEK}	RBSOA, Clamped inductive load; L = 100 µH	V_{CES}	
t_{SC} (SCSOA)	V_{CE} = V_{CES}; V_{GE} = ±15 V; R_G = 22 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	379	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$	I_C = 75 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.7	3.2	V
	T_{VJ} = 125°C		3.0		V
$V_{GE(th)}$	I_C = 2 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			3.7	mA
	T_{VJ} = 125°C			12.5	mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$	Inductive load, T_{VJ} = 125°C		100		ns
t_r	V_{CE} = 600 V; I_C = 60 A		70		ns
$t_{d(off)}$	V_{GE} = 15/0 V; R_G = 22 Ω		500		ns
t_f			70		ns
E_{on}			9.1		mJ
E_{off}			6.7		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		3.3		nF
R_{thJC}	(per IGBT)			0.33	K/W
R_{thJH}	with heatsink compound (0.42 K/m.K; 50 µm)		0.66		K/W

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL Release applied

Applications

- AC and DC motor control
- AC servo and robot drives
- Power supplies
- Welding inverters

Advantages

- Easy to mount with four screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight

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Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

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Reverse diodes (FRED)

Symbol	Conditions	Maximum Ratings	
I_{F25}	T_C = 25°C	100	A
I_{F80}	T_C = 80°C	60	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F	I_F = 60 A; T_{VJ} = 25°C		2.28	2.6	V
	T_{VJ} = 125°C		1.67		V
I_{RM}	I_F = 60 A; di_F/dt = 500 A/µs; T_{VJ} = 125°C		41		A
t_{rr}	V_R = 600 V; V_{GE} = 0 V		200		ns
R_{thJC}				0.66	K/W
R_{thJH}	with heatsink compound (0.42 K/m.K; 50 µm)		1.32		K/W

Temperature Sensor NTC

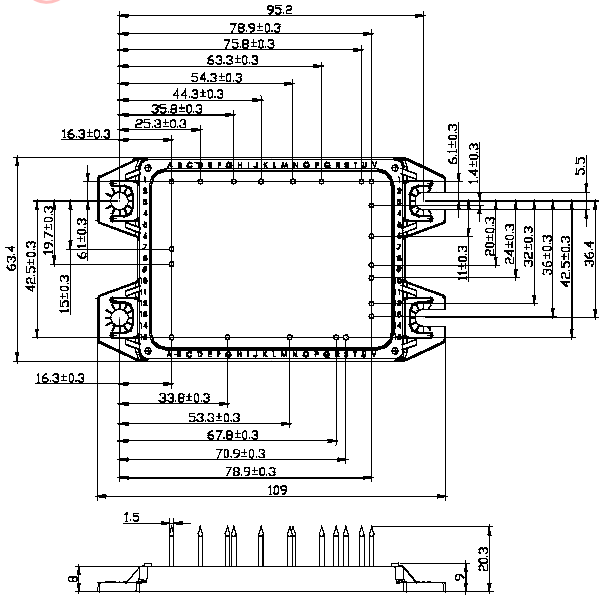
Symbol	Conditions	Characteristic Values min.	typ.	max.	
R_{25}	T = 25°C	4.75	5.0	5.25	kΩ
$B_{25/50}$			3375		K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+125	°C
T_{stg}		-40...+150	°C
V_{ISOL}	I_{ISOL} ≤ 1 mA; 50/60 Hz	3000	V~
M_d	Mounting torque (M5)	3	Nm
		26	lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values min.	typ.	max.	
d_S	Creepage distance on surface (Pin to heatsink)	11.2			mm
d_A	Strike distance in air (Pin to heatsink)	11.2			mm
Weight			86		g

Package style and outline
Dimensions in mm (1mm = 0.0394“)



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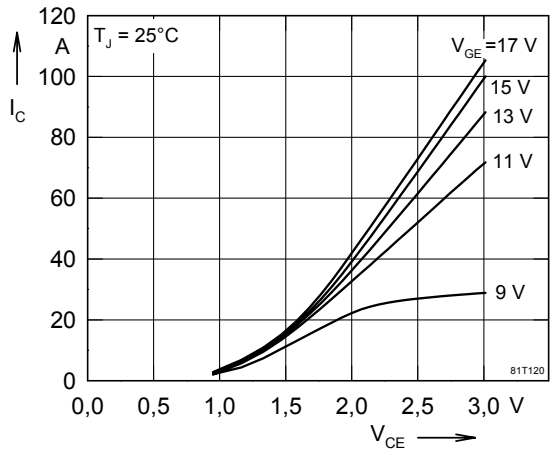

Fig. 1 Typ. output characteristics

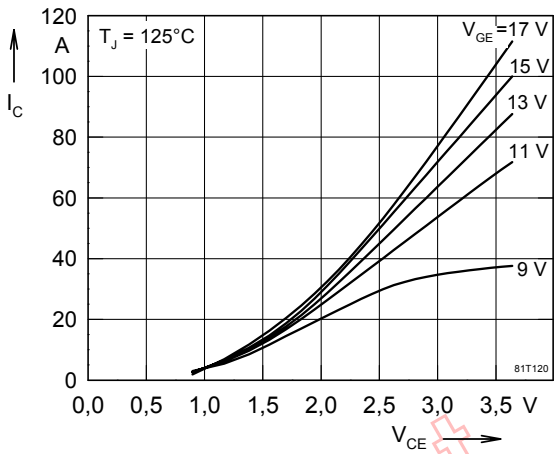

Fig. 2 Typ. output characteristics

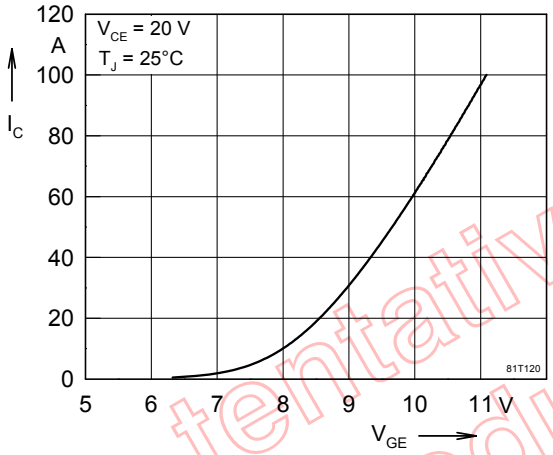

Fig. 3 Typ. transfer characteristics

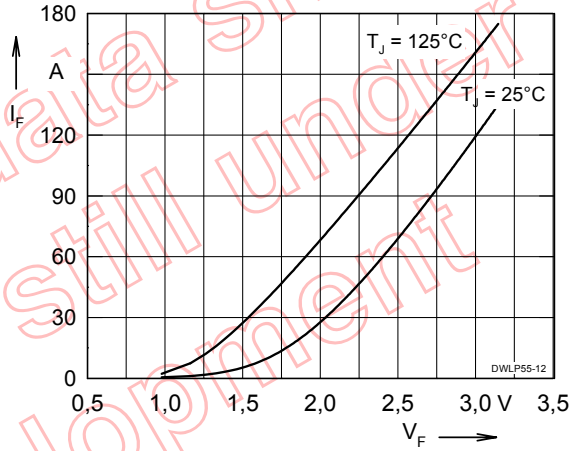

Fig. 4 Typ. forward characteristics of free wheeling diode

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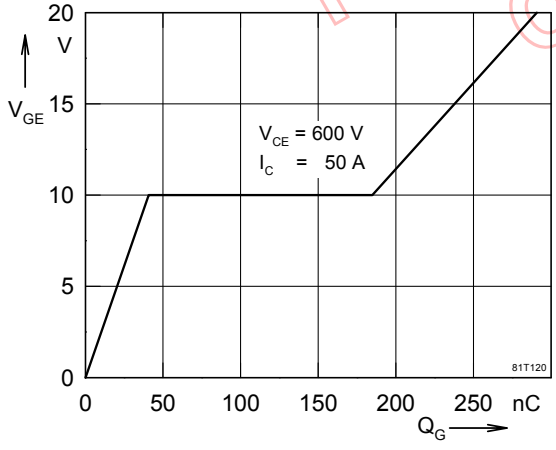

Fig. 5 Typ. turn on gate charge

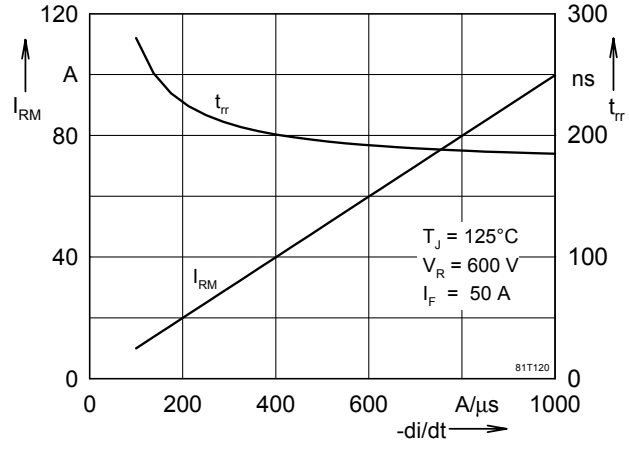

Fig. 6 Typ. turn off characteristics of free wheeling diode

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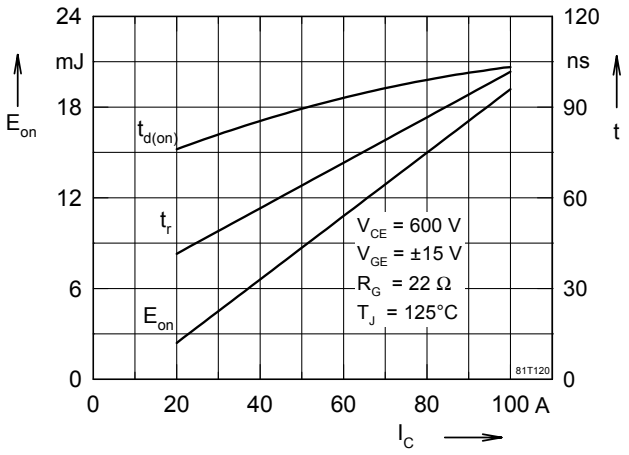

Fig. 7 Typ. turn on energy and switching

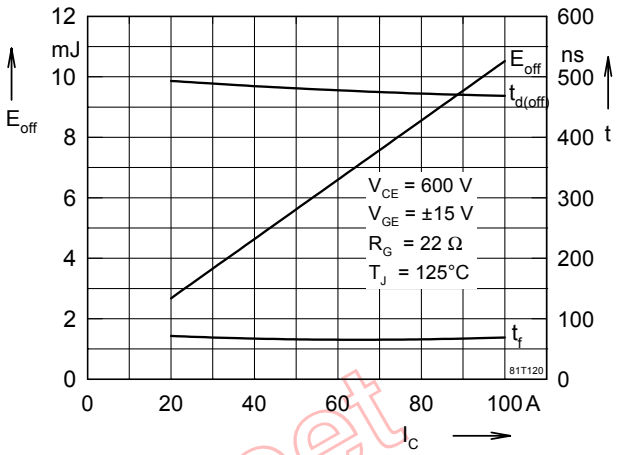

Fig. 8 Typ. turn off energy and switching times versus collector current times versus collector current

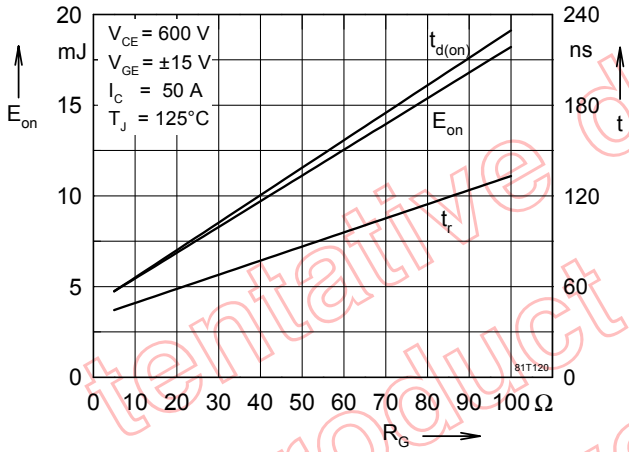

Fig. 9 Typ. turn on energy and switching

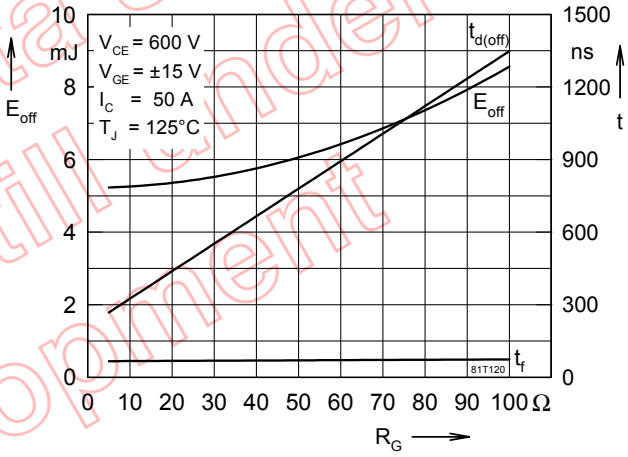

Fig. 10 Typ. turn off energy and switching times versus gate resistor times versus gate resistor

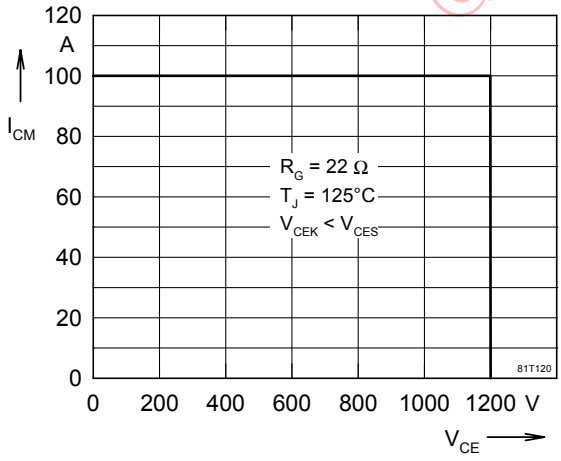

Fig. 11 Reverse biased safe operating area

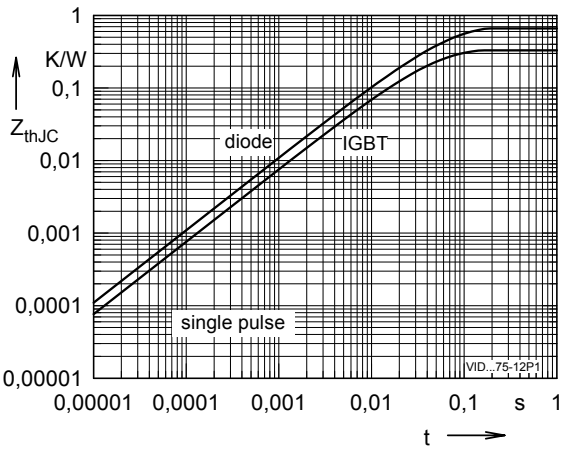

Fig. 12 Typ. transient thermal impedance RBSOA

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